

Supporting Information

Boosted Electron Transport and Enlarged Built-in Potential by Eliminating Interface Barrier in Organic Solar Cells

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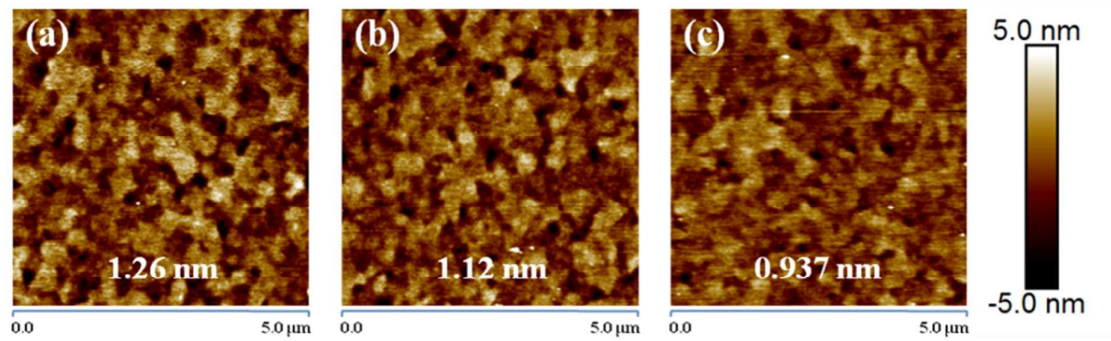


Figure S1. AFM images of (a) ITO/P₁, (b) ITO/P₂ and (c) ITO/P₃ composite films with a scale of 5 $\mu\text{m} \times 5 \mu\text{m}$.

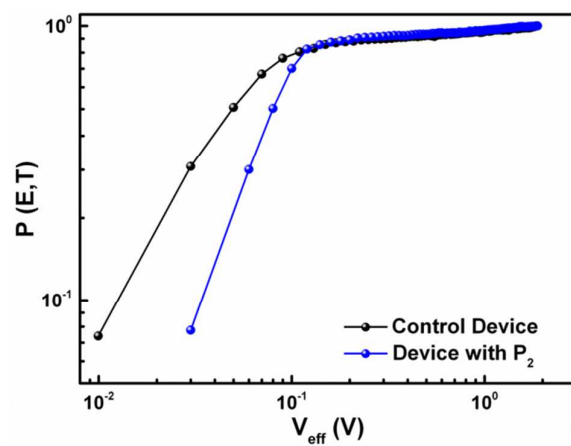


Figure S2. $P(E,T)$ versus V_{eff} characteristics of the control device and device with P_2 interlayer.

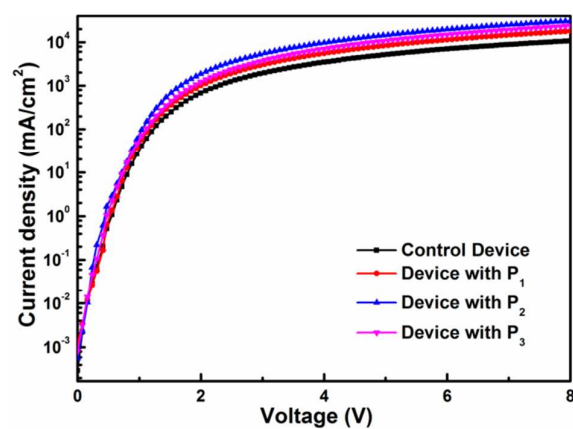


Figure S3. J - V characteristics curves of electron-only devices with the structure of ITO/TiO₂/PCDTBT:PC₇₁BM/BCP/Ag and ITO/TiO₂/P₁ or P₂ or P₃/PCDTBT:PC₇₁BM/BCP/Ag.